

Electronic Supporting Information for *J. Mater. Chem.* article by J. Choi and E. G. Gillan entitled “Low-temperature solvothermal synthesis of nanocrystalline indium nitride and Ga-In-N composites from the decomposition of metal azides”.

Figure S1. SEM of benchtop hexadecane reaction of $\text{InBr}_3 + 3 \text{NaN}_3$ at 275 °C.

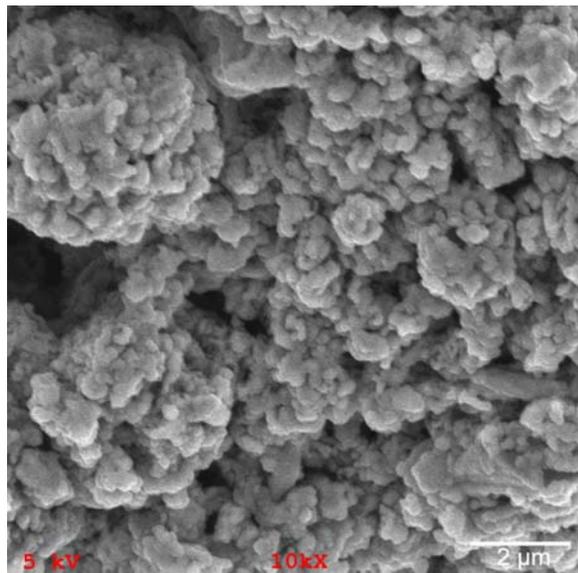


Figure S2. TEM of benchtop hexadecane reaction showing sheet-like aggregation. (scale bar = 50 nm)

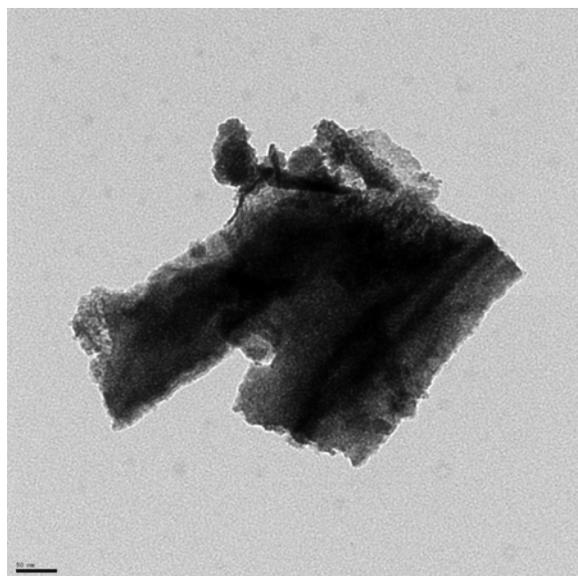


Figure S3. XRD of $\text{Ga}_{0.5}\text{In}_{0.5}\text{N}$ composite synthesized at 250 °C in toluene (top curve) and after inert annealing a loose powder at 1000 °C for 3 hrs (bottom curve).

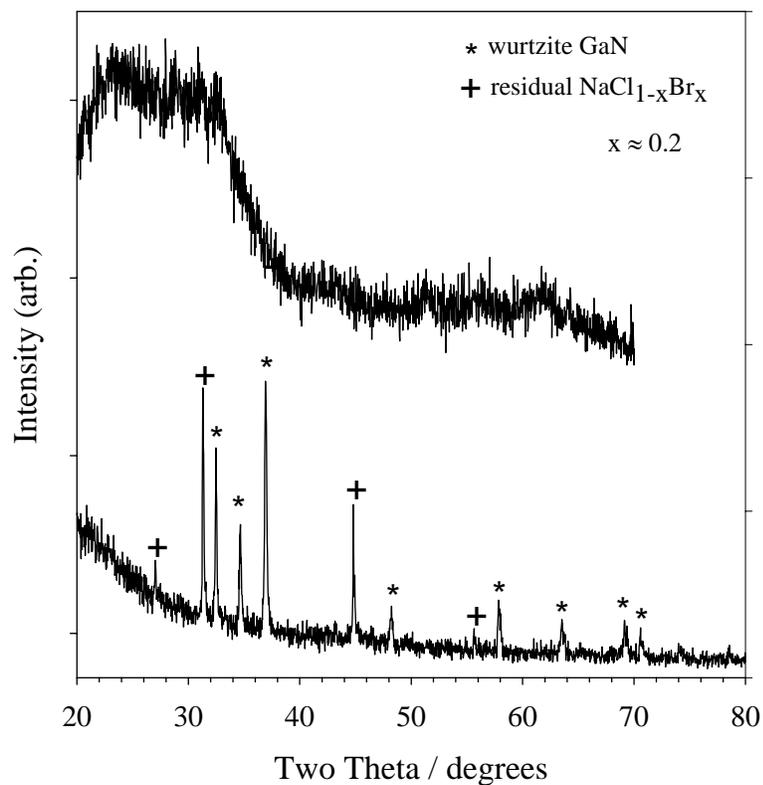


Figure S4. Solid UV-vis of InN powder from toluene reaction at 280 °C.

